2SC4965

Silicon NPN Epitaxial

HITACHI

ADE-208-006 1st. Edition

Application

VHF / UHF RF switch

Features

- Low Ron and high performance for RF switch.
- Capable of high density mounting.

Outline

CMPAK

3
1
1. Emitter
2. Base
3. Collector



2SC4965

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

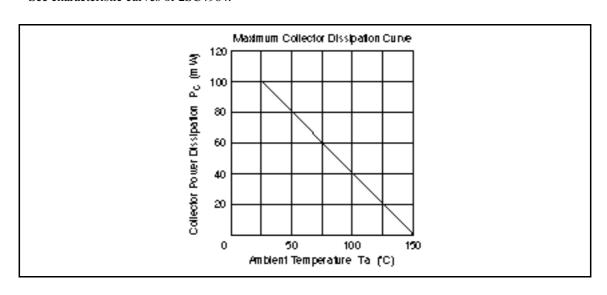
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I _c	100	mA
Collector power dissipation	P _c	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	12	_	_	V	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$
Collector cutoff current	I _{CBO}	—	_	10	μA	$V_{CB} = 10 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	1	mA	$V_{CE} = 8 \text{ V}, R_{BE} =$
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE}	100	250	600		$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	_	150	300	mV	$I_{\rm C}$ = 80 mA, $I_{\rm B}$ = 5 mA
Collector output capacitance	Cob	_	1.9	1.6	pF	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
On resistance	Ron	_	1.2	_		I _B = 2.5 mA, f = 1 kHz

Note: Marking is "YV-".

See characteristic curves of 2SC4964.



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